# 1200V/150A <br> THREE PHASE BRIDGE FEM WITH BRAKE <br> <br> M.S.KENNEDY CORP. <br> <br> M.S.KENNEDY CORP. <br> MST 

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## FEATURES:

- Full Three Phase Bridge Configuration with SCR/IGBT Brake
- 1200V Rated Voltage
- 150A Continuous Output Current
- Internal Zener Clamps on Gates
- Proprietary Encapsulation Provides Near Hermetic Performance
- MIL-PRF-38534 Screening Available (Modified)
- Light Weight Domed ALSIC Baseplate
- Robust Mechanical Design for Hi-Rel Applications
- Ultra-Low Inductance Internal Layout
- Withstands 96 Hours HAST and Thermal Cycling ( $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ )
- Contact MSK for MIL-PRF-38534 Qualification Status



## DESCRIPTION:

The MSK 4852 is one of a family of plastic encapsulated modules (PEM) developed specifically for use in military, aerospace and other severe environment applications. The Three Phase Bridge configuration along with the SCR/IGBT brake circuit and 1200 volt/ 150 amp rating make it ideal for use in high current motor drive and inverter applications. The Aluminum Silicon Carbide (AISiC) baseplate offers superior flatness and light w eight; far better than the copper or copper alloys found in most high pow er plastic modules. The high thermal conductivity materials used to construct the MSK 4852 allow high power outputs at elevated baseplate temperatures. Our proprietary coating, SEES ${ }^{\text {m }}$ - Severe Environment Encapsulation System - protects the internal circuitry of MSK PEM's from moisture and contamination, allow ing them to pass the rugged environmental screening requirements of military and aerospace applications. MSK PEM 's are also available with industry standard silicone gel coatings for a low er cost option.

## EQUVALENT SCHEMATIC



## TYPICAL APPLICATIONS

- Motor Drives
- Inverters


## ABSOLUTE MAXIMUM RATING

(10)

VCE
Vge
Iout
Collector to Emitter Voltage
Gate to Emitter Voltage
1200V
$\pm 20 \mathrm{~V}$
150A
300A
100A
ISCR/REG
ISCR/REG
Current (Continuous) 150A

VCASE Case Isolation Voltage
Tst Storage Temperature Range . . $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$
TJ J unction Temperature $150^{\circ} \mathrm{C}$

## Tc Case Operating Temperature Range

MSK $4852 \mathrm{H} / \mathrm{E}$. . . . . . . . $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$

MSK 4852
$-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$

## ELECTRICAL SPECIFICATIONS

| Parameter (6) | Test Conditions | Group A | MSK 4852 H/E |  |  | MSK 4852 |  |  | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Subgroup | Min. | Typ. | Max. | Min. | Typ. | Max. |  |
| Collector-Emitter Saturation Voltage 8 | 8) $\mathrm{IC}=150 \mathrm{~A}, \mathrm{VGE}=15 \mathrm{~V}$ | 1 | - | 1.9 | 2.5 | - | 1.9 | 2.6 | V |
|  |  | 2 | - | 2.3 | 2.9 | - | 2.3 | 3.0 | V |
|  |  | 3 | - | 1.9 | 2.5 | - | 1.9 | 2.5 | V |
| Collector-Emitter Saturation Voltage (7) | (7) $\mathrm{IC}=150 \mathrm{~A}, \mathrm{VGE}=15 \mathrm{~V}$ | 1,3 | - | 1.7 | - | - | 1.7 | - | V |
|  |  | 2 | - | 1.9 | - | - | 1.9 | - | V |
| Collector-Emitter Leakage Current | $\mathrm{VCE}=1000 \mathrm{~V}, \mathrm{VGE}=0 \mathrm{~V}$ | 1 | - | 0.05 | 6 | - | 0.05 | 8 | mA |
|  |  | 2 | - | 0.1 | 10 | - | 0.1 | 12 | mA |
|  |  | (1) 3 | - | 0.05 | 6 | - | 0.05 | 8 | mA |
| Gate Threshold Voltage | $\mathrm{IC}=6 \mathrm{~mA}, \mathrm{VCE}=\mathrm{VGE}$ | 1 | 4.0 | 5.8 | 6.5 | 4.0 | 5.8 | 6.6 | V |
|  |  | 2 | 3.5 | 5.0 | 6.0 | 3.5 | 5.0 | 6.1 | V |
|  |  | 3 | 4.0 | 5.9 | 6.6 | 4.0 | 5.9 | 6.7 | V |
| Gate Leakage Current | $V C E=0 V, V G E= \pm 15 \mathrm{~V}$ | 1,3 | -10 | 0.10 | 10 | -12 | 0.10 | 12 | UA |
|  |  | 2 | -10 | 0.15 | 10 | -12 | 0.15 | 12 | uA |
| Diode Forward Voltage (8) | $I C=150 A$ | 1 | - | 1.8 | 2.4 | - | 1.8 | 2.5 | V |
|  |  | 2 | - | 1.8 | 2.4 | - | 1.8 | 2.5 | V |
|  |  | 3 | - | 1.7 | 2.4 | - | 1.7 | 2.5 | V |
| Diode Forward Voltage (7) | $I C=150 \mathrm{~A}$ | 1,2 | - | 1.7 | - | - | 1.7 | - | V |
|  |  | 3 | - | 1.6 | - | - | 1.6 | - | V |
| SCR Reverse Leakage | VRRM $=1000 \mathrm{~V}$ | 1,2,3 | - | 0.01 | 10 | - | 0.01 | 12 | mA |
| SCR On Voltage (8) | $I F=100 A$ | 1 | - | 1.1 | 1.35 | - | 1.1 | 1.4 | V |
|  |  | 2 | - | 1.0 | 1.35 | - | 1.0 | 1.4 | V |
|  |  | 3 | - | 1.2 | 1.5 | - | 1.2 | 1.6 | V |
| SCR Holding Current |  | 1 | - | 100 | 300 | - | 100 | 325 | mA |
|  |  | 2 | - | 90 | 300 | - | 90 | 325 | mA |
|  |  | 3 | - | 110 | 300 | - | 110 | 325 | mA |
| Regen Diode Forward Voltage | $I F=50 A$ | 1 | - | 1.5 | 2.2 | - | 1.3 | 2.3 | V |
|  |  | 2 | - | 1.5 | 2.2 | - | 1.5 | 2.3 | V |
|  |  | 3 | - | 1.4 | 2.2 | - | 1.4 | 2.3 | V |
| Total Gate Charge (1) | $\mathrm{V}=600 \mathrm{~V}, \mathrm{IC}=150 \mathrm{~A}$ | 4 | - | 1000 | 1500 | - | 1000 | 1600 | nC |
| Turn-On Delay (1) V | $\mathrm{V}=600 \mathrm{~V}, \mathrm{IC}=150 \mathrm{~A}, \mathrm{RG}=20 \Omega$ | 4 | - | 300 | 450 | - | 300 | 475 | nS |
| Rise Time (1) V | $\mathrm{V}=600 \mathrm{~V}, \mathrm{IC}=150 \mathrm{~A}, \mathrm{RG}=20 \Omega$ | 4 | - | 70 | 110 | - | 70 | 120 | nS |
| E(on) (1) $\quad \mathrm{V}=600 \mathrm{~V}, \mathrm{IC}=15$ | $50 \mathrm{~A}, \mathrm{RG}=20 \Omega, \mathrm{VGE}=-7 /+15 \mathrm{~V}$ | 4 | - | 23 | - | - | 23 | - | mJ |
|  |  | 5 | - | 31 | - | - | 31 | - | mJ |
| E(off) (1) V $\quad \mathrm{C}=600 \mathrm{~V}, \mathrm{IC}=15$ | 50A, $\mathrm{RG}=10 \Omega, \mathrm{VGE}=-7 /+15 \mathrm{~V}$ | 4 | - | 12 | - | - | 12 | - | mJ |
|  |  | 5 | - | 17 | - | - | 17 | - | mJ |
| Turn-Off Delay (1) V | $\mathrm{V}=600 \mathrm{~V}, \mathrm{IC}=150 \mathrm{~A}, \mathrm{RG}=10 \Omega$ | 4 | - | 650 | 975 | - | 650 | 995 | uS |
| Fall Time (1) V | $\mathrm{V}=600 \mathrm{~V}, \mathrm{IC}=150 \mathrm{~A}, \mathrm{RG}=10 \Omega$ | 4 | - | 75 | 125 | - | 75 | 135 | nS |
| Diode Reverse Recovery Time (1) I | $\mathrm{IE}=150 \mathrm{~A}, \mathrm{di} / \mathrm{dt}=1250 \mathrm{~A} / \mathrm{uS}$ | 4 | - | 460 | 650 | - | 460 | 675 | nS |
| Diode Reverse Recovery Charge (1) I | $\mathrm{IE}=150 \mathrm{~A}, \mathrm{di} / \mathrm{dt}=1250 \mathrm{~A} / \mathrm{uS}$ | 4 | - | 13.4 | 20 | - | 13.4 | 25 | uC |
| Thermal Resistance (1) BR | IGBT @ TJ=125 ${ }^{\circ} \mathrm{C}$ | 4 | - | 0.16 | 0.2 | - | 0.16 | 0.21 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | BRIDGE DIODE @ $\mathrm{TJ}=125^{\circ} \mathrm{C}$ | 4 | - | 0.26 | 0.32 | - | 0.26 | 0.33 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | REGEN SCR | 4 | - | 0.16 | 0.2 | - | 0.16 | 0.21 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | REGEN DIODE | 4 | - | 0.35 | 0.43 | - | 0.35 | 0.44 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## NOTES:

(1) Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
(2) Industrial grade and "E" suffix devices shall be tested to subgroup 1 unless otherwise specified.
(3) Military grade devices ("H" suffix) shall be $100 \%$ tested to subgroups 1,2 and sample tested to subgroup 3 .
(4) Subgroups 4, 5 and 6 testing available upon request.
(5) Subgroup 1, $4 \mathrm{TA}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$
$2,5 \mathrm{TA}=+125^{\circ} \mathrm{C}$
$3,6 \mathrm{TA}=-55^{\circ} \mathrm{C}$
(6) All specifications apply to both the upper and lower sections of the half bridge.
(7) Measurements are made by forcing current through the power lugs and measuring the actual die drop at the small signal terminals. Measurements are provided for determining thermal dissipation on the IGBT/diode.
(8) Measurements includes die, substrate, wire bond and power lug.
(9) VGE $=15 \mathrm{~V}$ unless otherw ise specified.
(10) Continuous operation at or above absolute maximum ratings may adversly effect the device performance and/or life cycle.

## APPLICATION NOTES

## THERMAL CALCULATIONS

Pow er dissipation and maximum allow able temperature rise involve many variables w orking together. Collector current, PWM duty cycle and switching frequency all factor into power dissipation. DC losses or "ON-TIME" losses are simply VCE(SAT) x Collector Current x PWM duty cycle. For the MSK 4852, VCE(SAT) $=1.9 \mathrm{~V}$ typically, and at 150 amps and a PWM duty cycle of $30 \%$, DC losses equal 85.5 w atts. Switching losses, in milli-joules, vary proportionally with switching frequency. The MSK 4852 typical sw itching losses at $\mathrm{VCE}=600 \mathrm{~V}$ and $\mathrm{ICE}=150 \mathrm{~A}$ are about 48 mJ , which is simply the sum of the turn-on switching loss and the turn-off sw itching loss. Multiplying the switching frequency times the sw itching losses will result in a power dissipation number for sw itching. The MSK 4852, at 10 KHz , will exhibit switching power dissipation of 480 w atts. The total losses are the sum of DC losses plus sw itching losses, or in this case, 565.5 w atts total.
565.5 w atts $\times 0.20^{\circ} \mathrm{C} / \mathrm{W}$ thermal resistance equals 113 degrees of temperature rise betw een the case and the junction. Subtracting $113^{\circ} \mathrm{C}$ from the maximum junction temperature of $150^{\circ} \mathrm{C}$ equals $37^{\circ} \mathrm{C}$ maximum case temperature for this example.

VCE(SAT) $\times$ IC $\times$ PWM duty cycle $=1.9 \mathrm{~V} \times 150 \mathrm{amps} \times 30 \%=85.5 \mathrm{w}$ atts DC losses
Turn-on sw itching loss + Turn-off switching loss $=$ Total switching losses $=31+17=48 \mathrm{~mJ}$
Total sw itching loss $\times$ PWM frequency $=$ Total switching pow er dissipation $=48 \mathrm{~mJ} \times 10 \mathrm{KHz}=480 \mathrm{w}$ atts
Total power dissipation $=$ DC losses + switching losses $=85.5+480=565.5 \mathrm{w}$ atts
J unction temperature rise above case $=$ Total power dissipation x thermal resistance
565.5 w atts $\times 0.2^{\circ} \mathrm{C} / \mathrm{W}=113^{\circ} \mathrm{C}$ temperature rise above case

Maximum junction temperature - junction temperature rise $=$ maximum baseplate temperature

$$
150^{\circ} \mathrm{C}-113^{\circ} \mathrm{C}=37^{\circ} \mathrm{C}
$$

TBD

| OPERATION IN ACCORDANCE WITH MIL-PRF-38534 | INDUSTRIAL | CLASS E | CLASS H |
| :---: | :---: | :---: | :---: |
| QUALIFICATION (MODIFIED) | NO | NO | YES |
| ELEMENT EVALUATION | NO | YES | YES |
| CLEAN ROOM PROCESSING | YES | YES | YES |
| NON DESTRUCT BOND PULL SAMPLE | YES | YES | YES |
| CERTIFIED OPERATORS | NO | YES | YES |
| MIL LINE PROCESSING | YES | YES | YES |
| MAX REWORK SPECIFIED | NO | YES | YES |
| ENCAPSULANT | GEL COAT | SEES ${ }^{\text {TM }}$ | SEES ${ }^{\text {TM }}$ |
| PRE-CAP VISUAL | YES - INDUSTRIAL | YES - CLASS H | YES - CLASS H |
| TEMP CYCLE ( $-55^{\circ} \mathrm{C}$ TO $\left.+125^{\circ} \mathrm{C}\right)$ | NO | YES | YES |
| BURN-IN | NO | YES - 96 HOURS | YES - 160 HOURS |
| ELECTRICAL TESTING | YES - $25^{\circ} \mathrm{C}$ | YES - $25^{\circ} \mathrm{C}$ | YES - FULL TEMP |
| EXTERNAL VISUAL | YES - SAMPLE | YES - SAMPLE | YES |
| XRAY | NO | NO | NO |
| PIN FINISH | NI | NI | NI |

NOTE: ADDITIONAL SCREENING IS AVAILABLE SUCH AS XRAY, CSAM, MECHANICAL SHOCK, ETC. CONTACT FACTORY FOR QUAL STATUS.


ORDERING INFORMATION

## MSK4852 H

## SCREENING

BLANK = INDUSTRIAL; E=EXTENDED RELIA BILITY;
H= MIL-PRF-38534 CLASS H (MODIFIED)

## GENERAL PART NUMBER

THE ABOVE EXAMPLE IS A MILITARY SCREENED MODULE.

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